

insulating layer thicker than said first insulating layer on said first insulating layer;  
and

wherein a wiring in connection to said circuit electrode is  
formed on said second insulating layer.

26. A method according to claim 25, wherein said second insulating layer  
has a thickness of from 35  $\mu\text{m}$  to 150  $\mu\text{m}$ .

27. A method according claim 25, wherein said second insulating layer has  
an inclined portion.

28. A method according to claim 27, wherein said inclined portion has an  
average gradient of from 5 % to 30 %.

29. A method according to claim 25, wherein said second insulating layer  
is formed by printing with a polyimide paste.

30. A method according to claim 25, wherein said second insulating layer  
is formed by printing with a resin containing particles therein.

31. A method according to claim 25, wherein said second insulating layer  
is formed by printing with a thermosetting resin and heating.

32. A method according to claim 25, wherein said second insulating layer  
is formed by printing and heating.

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33. A method according to claim 25, wherein said mask used in said printing for formation of the second insulating film has openings smaller than an area of said second insulating layer.

34. A method according to claim 33, wherein said printing for formation of the second insulating film is performed by:

aligning said mask and a pattern on said wafer with each other;

filling a resin into said openings in said mask by moving a squeegee on said mask; and

separating said mask from said wafer.

35. A method according to claim 25, further comprising the step of forming an external connection terminal connected to said wiring.

36. A method according to claim 25, further comprising the step of forming a third electrically insulating layer covering said second insulating layer and said wiring.

37. A method according to claim 25, further comprising the step of forming a surface protective layer covering said second insulating layer and said wiring.

38. A method according to claim 25, further comprising the step of dicing said wafer. --

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